Technical Digest

The 18th International Conference on Crystal Growth and Epitaxy

ICCGE-18

Nagoya, Japan August 7th - 12th, 2016

in conjunction with

The 16th International Summer School on Crystal Growth

ISSCG-16

Lake Biwa, Shiga, Japan August 1st - 7th, 2016



Program at a Glance

	Aug. 7 (Sun)	Aug. 8 (Mon)	Auç	g. 9 (Tue)	Aug. 10 (Wed)	Aug. 11 (Thu)		Aug 12 (Fri)
8:00	ана на		Registration		Registration	Registration		Registration
			Award 3 Plenary 4 Hu and Chen Coffee Break		Plenary 5 Amano	Plenary 6 Ross Coffee Break		Plenary 7 Kuech Coffee Break Fr1 G06, G09, G11, T02, T03, T04, T05, T06, T08, T10
9:00		Ceremony Plenary 1 Akasaki			Coffee Break			
40.00					We1 G01, G03, G05, G06, J01, T01, T04, T06, T09	Th1 G01, G03, G05, G06, G09, T01, T02, T03, T04,		
10:00	8		Tu1 G01, G02, G03,					
11:00			G04, G06, G07, G08, G10, T07, T09	T06				
12:00		Lunch		IOCG Executive Committee Meeting		Lunch	IOCG Council Meeting	Closing
			Lunch					
13:00						A CONTRACTOR OF A DECISION	OCG	
44:00		Plenary 2	Tu2 G01, G02, G03, G04, G06, G07, G08, J01, T07,	Tu2		Assembly		¥.
14:00	JACG Meeting	Galazka Plenary 3 Frenkel		G02, G03, G06, G07,		Th2 G06, G09, G11,		
15:00		Award 1 Award 2	T09			T02, T03, T04, T05, T06, T08, T10		
16:00	Registration	Coffee Break		fee Break				
		Mo1 G01, G02, G03, G04, G07, G08, G10, T07, T09	Tu3 G01, G03, G04,	Excursion	a color of the second second	Poster 3		
17:00			G05, G06, G07, J01, T01, T06, T09			G06, G09, G11, T02, T03, T04, T05, T08, T10		
18:00								
19:00	Welcome Reception	Poster 1 G01, G02, G03,	G05, J01,	oster 2 G06, G10, T01, T06, T09				
20:00		G04, G07, G08, T07				В	anquet	
		U		••••••••••••••••••••••••••••••••••••••				

-12 -

performance of grown crystals, the Ga and Ge contents of the crystal were tuned in this study by changing the composition of raw materials. It was found that the Ga content of the crystal linearly increases with that of the raw material. The clathrate with Ga content of 16.7 possesses the highest power factor of $2x10^{-3}$ Wm⁻¹K⁻² at 500 degree C, as this sample also possesses the highest electrical conductivity among all samples.

18:40 MoP-T07-6 Poster (120 min)

Investigation of relaxor-PT single crystals for practical applications

H. Luo*, X. Zhao, W. Di, H. Deng, X. Li Shanghai Institute of Ceramics, Chinese Academy of Sciences, China

More than 3 inches in diameter PMN-PT and PIN-PMN-PT single crystals are grown along (001) by the modified Bridgman technique for mass production in SICCAS. These relaxor-PT crystals exhibit not only extrahigh piezoelectric performances, but also excellent optoelectric and pyroelectric performances. They are good candidates for the next generation of ultrasonic transducers, actuators, transformers and infrared detectors etc.

18:40 MoP-T07-7 Poster (120 min)

The effect of complex electrodeposition by the addition of Multi-layered graphene on copper nanoparticles

Y.-L. Cho¹*, J.-W. Lee¹, Y.-I. Song², C. Park³, S.-J. Suh²

¹School of Advanced Materials Science & Engineering, ²Advanced Materials and Process Research for IT, Sungkyunkwan University, Korea, ³Pukyoung National University, Korea

We demonstrated complex electroplating of metal nanoparticles with multi-layered graphene films. Complex electroplating was carried out in an electrolyte, and multi-layered graphene coated copper nanoparticles (MGCNs) were created using an electrical explosion method, which is an easy technique of creating nanoparticles. The MGCNs had a diameter smaller than 100 nm and a copper core-shell structure with multiple layers of graphene. Cyclic voltammetry was performed to analyze the electrochemical behavior of the MGCNs. The microstructure and particle size of the MGCNs was also observed using TEM and Raman spectroscopy. The resistivity of the copper electroplating was 2.28×10⁻⁶ ohm cm, and the resistivity of the complex electroplated MGCNs was decreased by 12.7% to 1.99×10-6 ohm cm. Owing to their lower resistivity, MGCNs can be used in copper interconnections for PCB or semiconductor processes.

18:40 MoP-T07-8 Poster (120 min)

Single crystal growth and exploration of new ironbased superconductors in Ca-*RE*-Fe-As system

II. Ogino^{1,2} *, H. Yakita¹, A. Sala², A. Iyo², H. Eisaki², J. Shimoyama³, K. Kishio¹

¹The University of Tokyo, Japan, ²National Institute of Advanced Industrial Science and Technology, Japan, ¹Aoyama Gakuin University, Japan

After the discovery of high- T_c superconductivity in in LaFeAs(O,F), many Fe-based superconductors were discovered. In order to clarify the origin of

superconductivity in Ca-RE-Fe-As system, we have grown Pr doped CaFe₂As₂ single crystals. These samples showed two-step transitions at $T_{e1} \sim 40$ K, and $T_{e2} \sim 20$ K. However, the superconducting volume fraction above T_{e2} was always very low, indicating that 40 K-class superconductivity is not originated from the bulk superconductivity. On the other hand, we have discovered another compound (Ca,RE)FeAs₂. Crystal structure of the (Ca,Pr)FeAs₂ is composed of Ca(Pr) planes, Fe₂As₂ layer chain layer. (Ca,Pr)FeAs₂ showed and As_2 superconductivity with up to $T_c \sim 30$ K. From the measurement of anisotoropy, the compoud show exceptionaly low anistropy considering its relatively large c-axis length. Such feature is attributed to the structure of the blocking layer, and this may lead to new class of ironbased superconductor with high T_c and low anistropy.

18:40 MoP-T07-9 Poster (120 min)

Crystal Structure and Luminescence properties of the Novel $KSrR(BO_3)_2$ with R = Y, Tb, Yb

A. K. Bolatov¹*, A. E. Kokh², N. G. Kononova², V. S. Shevchenko², Yu. V.Seryotkin^{2,3}, Kh. A. Abdullin¹, B. M. Uralbekov¹, M. Burkitbayev¹

¹Al-Farabi Kazakh National University, Kazakhstan, ²V.S. Sobolev Institute of Geology and Mineralogy SB RAS, Russia, ³Novosibirsk state university, Russia

A new borate KSrY(BO₃)₂ was obtained by solid state synthesis and spontaneous crystallization using selected flux. In addition, two isostructural compounds KSrTb(BO₃)₂ and KSrYb(BO₃)₂ were also prepared using solid state techniques. KSrY(BO₃)₂ crystallizes in monoclinic space group P21/m. The base building block for this structure is the two-layer {Y[KSr(BO₃)₂]} package with one package on c-period. The infrared spectrum indicates that the KSrR(BO₃)₂ compounds contain characteristic (BO₃)³⁻ groups as its basic structural units, which is in agreement with the single crystal X-ray diffraction studies.

18:40 MoP-T07-10 Poster (120 min)

Field-induced phase transition and electromechanical properties of PLZST antiferroelectric single crystal Q. Li¹*, J. H. Gao¹, F. P. Zhuo¹, Q. F. Yan¹, Y. L. Zhang²

¹Department of Chemistry, ²State Key Laboratory of New Ceramics and Fine Processing, Tsinghua University, China

PLZST single crystal near MPB was proved to possess an antiferroelectric and ferroelectric phase coexistence structure, with the AFE phase dominated, at room temperature. Temperature dependent polarization measurement indicated that AFE phase could be induced into a metastable field induced FE phase. A temperature induced phase transition from induced FE to AFE state had been proved by its electric measurement. And a remarkable strain of 0.75% was obtained.

18:40 MoP-T07-11 Poster (120 min)

Multiscale investigation of electronic structures and optical properties induced by mc-Si defects on solar cell performance

O. A. Al-Ani^{*}, J. P. Goss, A. M.A. Sabaawi, P. R. Briddon, M. J. Rayson, N. E. B. Cowern *Newcastle University, UK*

The optical and electronic properties of silicon due point